

描述 / Descriptions

TO-92 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-92 Plastic Package.

特征 / Features

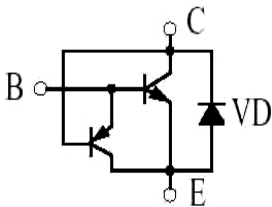
击穿电压稳定、开关速度快。

High Voltage, High Switching Speed.

用途 / Applications

用于充电器等开关电路。

Suitable for electrocircuit of charger ect..

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : Base PIN 2 : Collector PIN 3 : Emitter

放大及印章代码 / hFE Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

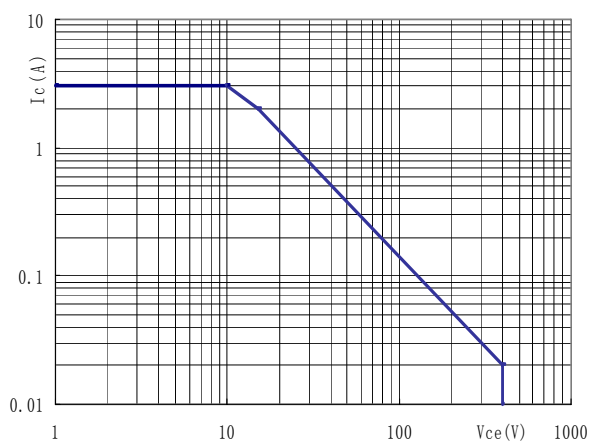
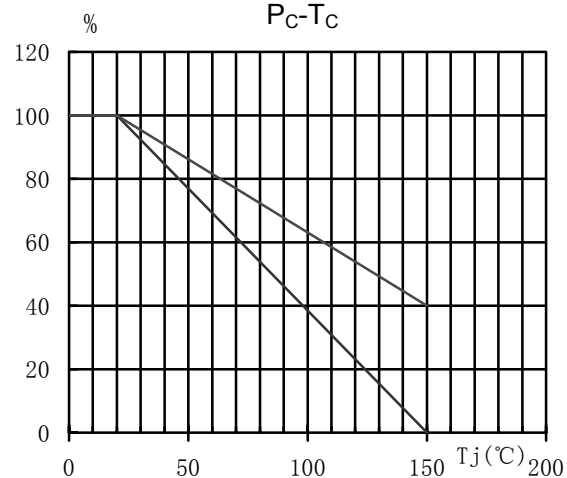
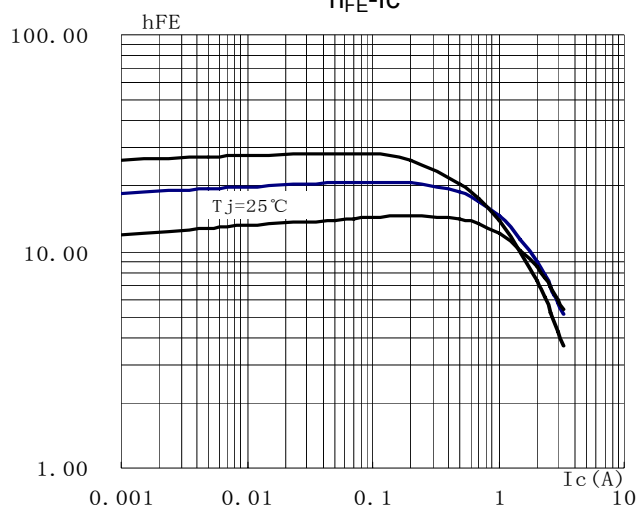
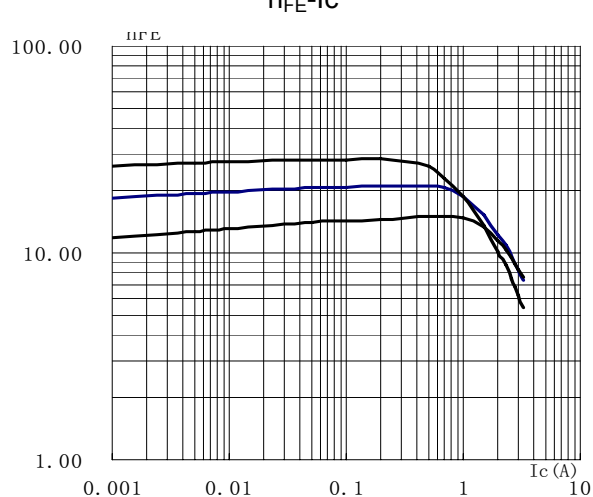
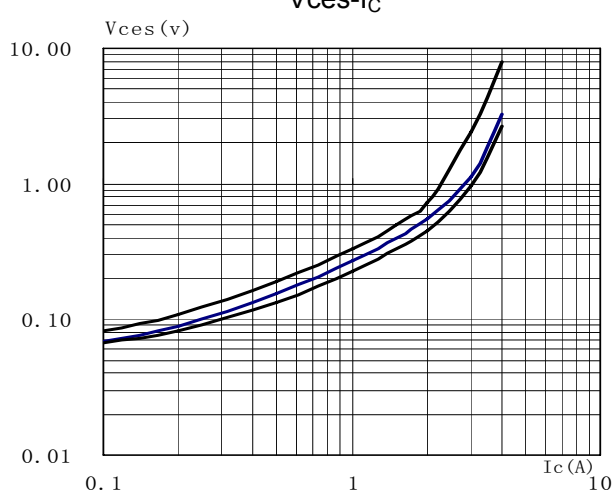
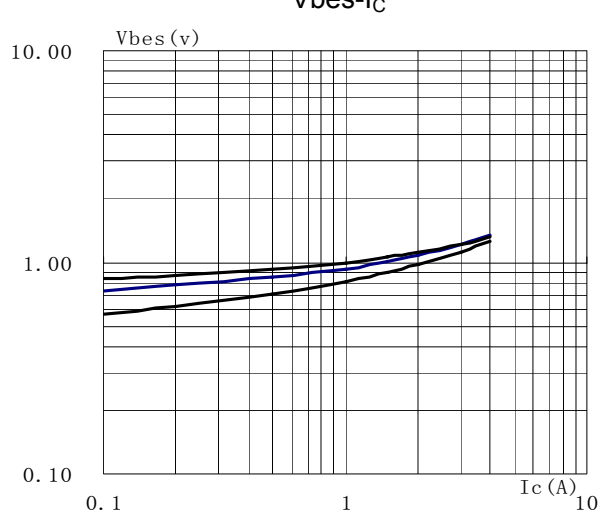
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	850	V
Collector to Emitter Voltage	V_{CEO}	450	V
Emitter to Base Voltage	V_{EBO}	9.0	V
Collector Current - Continuous	I_C	3.5	A
Collector Power Dissipation	P_C	1.2	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1mA$ $I_E=0$	850			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	450			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=1mA$ $I_C=0$	9.0			V
Forward Voltage	V_F	$I_F=1.5A$			2.6	V
Collector cut-off current	I_{CEO}	$V_{CB}=850V$			100	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{CE}=450V$ $I_B=0$			250	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=10mA$	7			
	$h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=0.5A$	20		40	
	$h_{FE(3)}$	$V_{CE}=5.0V$ $I_C=3.5A$	5			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=1.0A$ $I_B=0.2A$			0.5	V
	$V_{CE(sat)(2)}$	$I_C=3.0A$ $I_B=0.75A$			1.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.0A$ $I_B=0.5A$			1.6	V
Fall time	t_f	$V_{CC}=5V$ $I_C=0.25A$ (UI9600)	3.5		4.5	μs
Storage time	t_s				0.5	μs


电参数曲线图 / Electrical Characteristic Curve

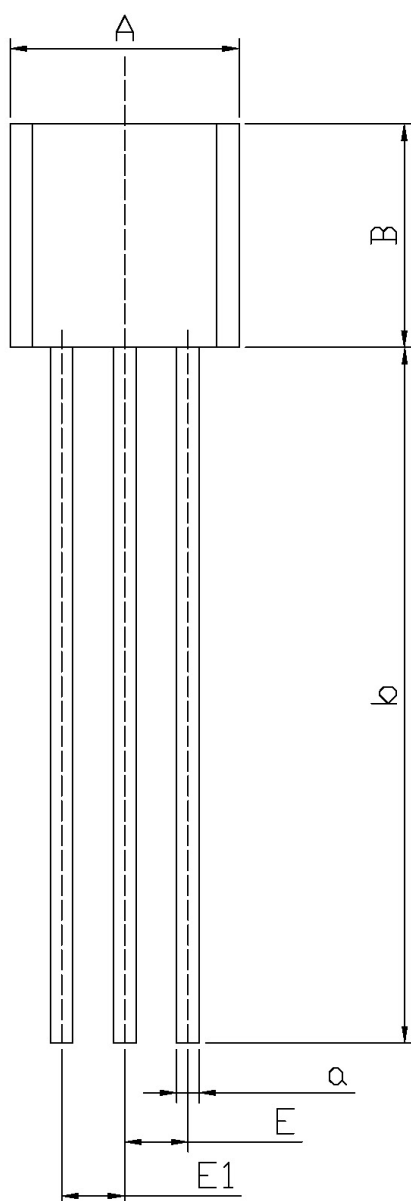
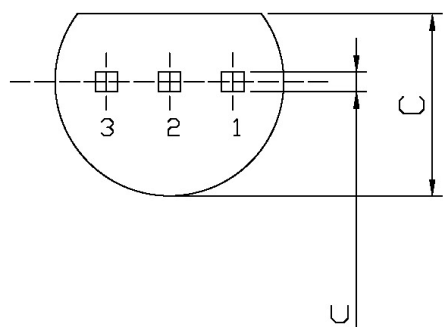
SOA(DC)

P_C-T_Ch_{FE}-I_Ch_{FE}-I_CV_{ces}-I_CV_{bes}-I_C

外形尺寸图 / Package Dimensions

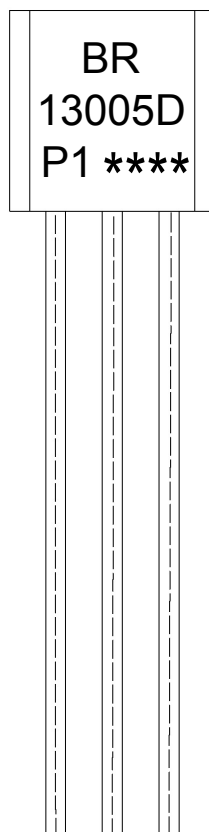
T0-92

Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.4	4.8
B	4.3	4.7
b	13	15
a	0.40	0.60
E	1.22	1.32
E1	1.22	1.32
C	3.4	3.8
c	0.30	0.50

印章说明 / Marking Instructions



说明：

BR: 为公司代码

13005D： 为型号代码

P1: 规格代码

****： 为生产批号代码，随生产批号变化。

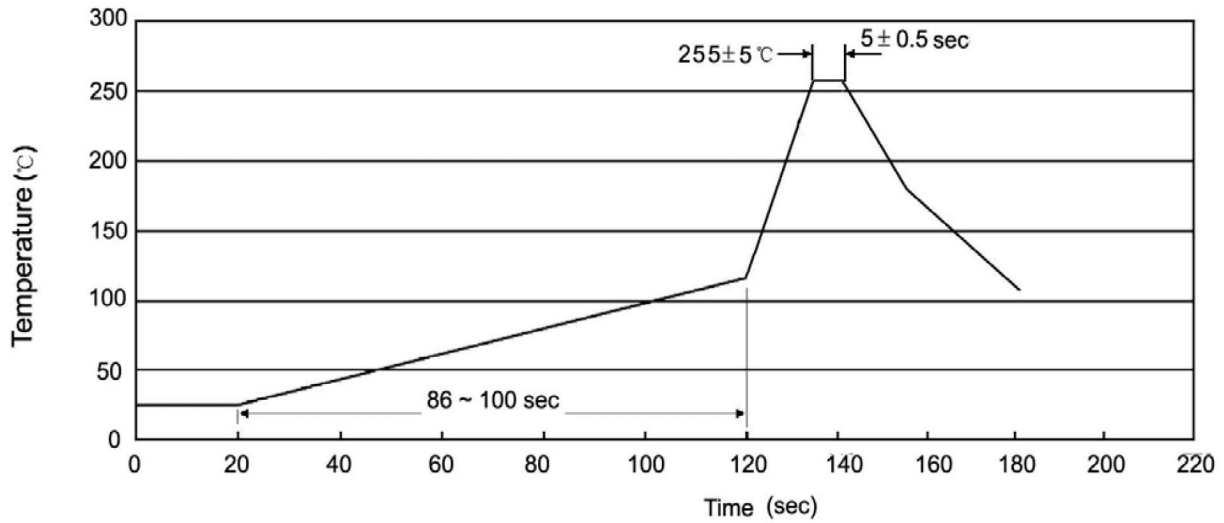
Note:

BR: Company Code.

13005D: Product Type.

P1: Specification Code.

****: Lot No. Code,code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)


说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

编带包装 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

使用说明 / Notices